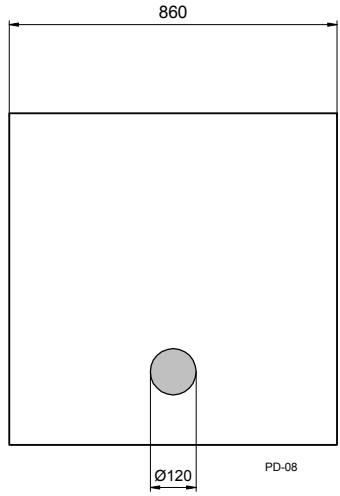


Wavelength range	Type	Technology	Electrodes
Red, selective	Integrated filter	AlGaAs/GaAs	P (anode) up

	typ. dimensions (µm)	
	<u>typ. thickness</u> 260 µm <u>anode</u> gold alloy, 1.5 µm <u>cathode</u> gold alloy, 0.5 µm	Description red-selective photodiode with narrow response range (660 nm peak) Applications Optical communications, safety equipment, light barriers

Miscellaneous Parameters

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Active area		A	0.73	mm ²
Operating temperature range		T_{amb}	-40 to +125	°C
Storage temperature range		T_{stg}	-40 to +125	°C

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Peak sensitivity	$V_R = 0\text{ V}$	λ_P		660		nm
Spectral range at 50 %	$V_R = 0\text{ V}$	$\lambda_{0.5}$	610		700	nm
Responsivity at λ_P^1	$V_R = 0\text{ V}$	S_λ	0,25	0.3		A/W
Responsivity at λ_P^2	$V_R = 0\text{ V}$	S_λ		0.45		A/W
Spectral bandwidth at 50%	$V_R = 0\text{ V}$	$\Delta\lambda_{0.5}$		90		nm
Dark current	$V_R = 1\text{ V}$	I_D		40	300	pA
Junction capacitance	$V_R = 0\text{ V}$	C_J		160		pF
Switching time	$V_R = 1\text{ V}$	t_r, t_f		200		ns

¹Measured on bare covered chip on TO-18 header

²Measured on epoxy covered chip on TO-18 header

Labeling

Type	Typ. I_D [pA]	Typ. S_λ [A/W]	Lot N°	Quantity
EPC-660-0.9-1				

Packing: Chips on adhesive film with wire-bond side on top

*Note: All measurements carried out with *EPIGAP* equipment

Typical responsivity spectrum